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Terms	Documents
L5 and damascene	3

Database:

US Patents Full-Text Database
 US Pre-Grant Publication Full-Text Database
 JPO Abstracts Database
 EPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L6

Refine Search

Recall Text

Clear

Search HistoryDATE: Sunday, June 29, 2003 [Printable Copy](#) [Create Case](#)**Set Name Query**

side by side

Hit Count Set Name
result set

DB=USPT; PLUR=YES; OP=ADJ

<u>L6</u>	L5 and damascene	3	<u>L6</u>
<u>L5</u>	L4 and (parallel adj plate)	19	<u>L5</u>
<u>L4</u>	L2 and (rf adj power)	76	<u>L4</u>
<u>L3</u>	L2 and (n2o or n2o3 or n2o4 or no2)	4	<u>L3</u>
<u>L2</u>	(insulating) near3 (silane or sif4 or oxygen)	813	<u>L2</u>
<u>L1</u>	(silicon near3 insulat?) and (fluorine near3 insulat?)	0	<u>L1</u>

END OF SEARCH HISTORY

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1. Document ID: US 6558756 B2

L6: Entry 1 of 3

File: USPT

May 6, 2003

US-PAT-NO: 6558756

DOCUMENT-IDENTIFIER: US 6558756 B2

TITLE: Method of forming interlayer insulating film

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC
Draw Desc	Image										

2. Document ID: US 6358838 B2

L6: Entry 2 of 3

File: USPT

Mar 19, 2002

US-PAT-NO: 6358838

DOCUMENT-IDENTIFIER: US 6358838 B2

TITLE: Semiconductor device and process for producing the same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC
Draw Desc	Image										

3. Document ID: US 5989998 A

L6: Entry 3 of 3

File: USPT

Nov 23, 1999

US-PAT-NO: 5989998

DOCUMENT-IDENTIFIER: US 5989998 A

TITLE: Method of forming interlayer insulating film

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC
Draw Desc	Image										

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Terms	Documents
L5 and damascene	3

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WEST[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 4 of 4 returned.**

1. Document ID: US 6548366 B2

L3: Entry 1 of 4

File: USPT

Apr 15, 2003

US-PAT-NO: 6548366

DOCUMENT-IDENTIFIER: US 6548366 B2

TITLE: Method of two-step annealing of ultra-thin silicon dioxide layers for uniform nitrogen profile

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KOMC
Draw Desc	Image									

2. Document ID: US 6503846 B1

L3: Entry 2 of 4

File: USPT

Jan 7, 2003

US-PAT-NO: 6503846

DOCUMENT-IDENTIFIER: US 6503846 B1

TITLE: Temperature spike for uniform nitridization of ultra-thin silicon dioxide layers in transistor gates

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KOMC
Draw Desc	Image									

3. Document ID: US 5888855 A

L3: Entry 3 of 4

File: USPT

Mar 30, 1999

US-PAT-NO: 5888855

DOCUMENT-IDENTIFIER: US 5888855 A

TITLE: Method of manufacturing active matrix display

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KOMC
Draw Desc	Image									

4. Document ID: US 5605867 A

L3: Entry 4 of 4

File: USPT

Feb 25, 1997

US-PAT-NO: 5605867

DOCUMENT-IDENTIFIER: US 5605867 A

TITLE: Method of manufacturing insulating film of semiconductor device and apparatus for carrying out the same

[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#) | [KIMC](#)

[Draw Desc](#) | [Image](#)

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Terms	Documents
L2 and (n2o or n2o3 or n2o4 or no2)	4

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